

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	123535	(field\$4 NEAR3 effect\$4 NEAR3 transistor\$4) OR FET OR MOS\$1FET	US-PGPUB; USPAT	OR	OFF	2005/11/09 11:34
L2	854	L1 AND etch\$4 AND (((hydrogen\$4 ADJ bromide\$4) OR HBr) WITH (chlori\$4 OR Cl2 OR "Cl.sub.2"))	US-PGPUB; USPAT	OR	OFF	2005/11/09 11:34
L3	516	L2 AND side\$1wall\$4	US-PGPUB; USPAT	OR	OFF	2005/11/09 11:31
L4	483	L3 AND poly\$1silicon	US-PGPUB; USPAT	OR	OFF	2005/11/09 11:32
L6	112	L4 AND (optical\$4 OR scatteromet\$4)	US-PGPUB; USPAT	OR	OFF	2005/11/09 11:33
L7	12762	((438/5,9,14,16,714,719,720,721,723,724,740,743,744) or (216/60,67,79) or (430/5)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/11/09 11:33
L9	22	L6 AND L7	US-PGPUB; USPAT	OR	OFF	2005/11/09 11:34
L10	106004	(field\$4 NEAR3 effect\$4 NEAR3 transistor\$4) OR FET OR MOS\$1FET	EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 11:34
L11	12	L10 AND etch\$4 AND (((hydrogen\$4 ADJ bromide\$4) OR HBr) WITH (chlori\$4 OR Cl2 OR "Cl.sub.2"))	EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 11:34